L Number	Hits	Search Text	DB	Time stamp
12	528	438/687,618,633,627,643,687.CCLS. and	USPAT;	2004/03/08 08:03
	ļ ·	((barrier or diffus\$5) adj (layer or	US-PGPUB;	
		film)) and (expos\$3 or treat\$6) and	EPO; JPO;	
		((reduc\$3 adj gases) or (hydrogen or	DERWENT;	
13	3489	("H.sub.2"))) and @ad<=20010417 438/\$.CCLS. and ((barrier or diffus\$5) adj	IBM_TDB USPAT;	2004/03/08 08:03
13	3489	(layer or film)) and (expos\$3 or treat\$6)	US-PGPUB;	2004/03/06 06:03
		and ((reduc\$3 adj gases) or (hydrogen or	EPO; JPO;	
	}	("H.sub.2"))) and @ad<=20010417	DERWENT;	
			IBM_TDB	
15	498	438/687,618,633,627,643,687.CCLS. and	USPAT;	2004/03/08 08:04
		(barrier adj (layer or film)) and (expos\$3	US-PGPUB;	
		or treat\$6) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))) and	EPO; JPO; DERWENT;	
		@ad<=20010417	IBM TDB	
14	239	438/687,618,633,627,643,687.CCLS. and	USPAT;	2004/03/08 08:04
		(barrier adj (layer or film)) and	US-PGPUB;	
	!	((expos\$3 or treat\$6) same ((reduc\$3 adj	EPO; JPO;	
		gases) or (hydrogen or ("H.sub.2")))) and	DERWENT;	
		@ad<=20010417	IBM_TDB	
-	833	438/618	USPAT;	2003/03/10 10:42
			EPO; JPO; DERWENT	
_	672	438/633	USPAT;	2001/12/17 14:40
	0,2	1.50, 555	EPO; JPO;	
			DERWENT	
-	45384	barrier adj (layer or film)	USPAT;	2001/12/18 14:06
			EPO; JPO;	
	1055		DERWENT	0004/00/00 00 50
-	1055	(barrier adj (layer or film)) and (reduc\$4	USPAT; EPO; JPO;	2004/03/02 08:58
	!	adj (gas or agent or chemical))	DERWENT	
_	237	((barrier adj (layer or film)) and	USPAT;	2001/12/18 08:17
		(reduc\$4 adj (gas or agent or chemical)))	EPO; JPO;	2002, 22, 20 0012,
		and (metal adj (film or layer))	DERWENT	
_	5	(barrier adj (layer or film)) and (first	USPAT;	2001/12/17 14:56
		adj reduc\$4 adj (gas or agent or	EPO; JPO;	
_	0	chemical))	DERWENT	2001/12/17 14.52
_	0	((barrier adj (layer or film)) and (first adj reduc\$4 adj (gas or agent or	USPAT; EPO; JPO;	2001/12/17 14:53
		chemical))) and (metal adj (film or	DERWENT	
		layer))		
_	0	(((barrier adj (layer or film)) and	USPAT;	2001/12/17 14:55
		(reduc\$4 adj (gas or agent or chemical)))	EPO; JPO;	
		and (metal adj (film or layer))) and	DERWENT	
		(second adj reduc\$4 adj (gas or agent or		
_	237	chemical)) (((barrier adj (layer or film)) and	USPAT;	2001/12/17 14:55
	231	(((barrier ad) (layer of lilm)) and (reduc\$4 adj (gas or agent or chemical)))	EPO; JPO;	2001/12/1/ 14:55
		and (metal adj (film or layer))) and	DERWENT	
		(reduc\$4 adj (gas or agent or chemical))		
-	163	(first adj reduc\$4 adj (gas or agent or	USPAT;	2001/12/17 14:58
		chemical))	EPO; JPO;	
		//Einah add mady-64 - 34 /	DERWENT	2001/10/13 15 65
_	92	((first adj reduc\$4 adj (gas or agent or chemical))) and (second adj reduc\$4 adj	USPAT; EPO; JPO;	2001/12/17 15:01
		(gas or agent or chemical))	DERWENT	
_	6		USPAT;	2001/12/17 15:01
		chemical))) and (second adj reduc\$4 adj	EPO; JPO;	
		(gas or agent or chemical))) and	DERWENT	
		semiconductor		
-	683	438/627	USPAT;	2001/12/17 15:31
			EPO; JPO;	
_	1178	438/643	DERWENT USPAT;	2002/01/02 14:19
, =	11/0	130,013	EPO; JPO;	2002/01/02 14:19
	[DERWENT	
_	20851	(((diffus\$6 adj barrier) or prevent\$10)	USPAT;	2001/12/18 14:01
		adj (layer or film))	EPO; JPO;	
			DERWENT	

,				
-	394	((((diffus\$6 adj barrier) or prevent\$10) adj (layer or film))) and (reduc\$4 adj	USPAT; EPO; JPO;	2001/12/18 08:17
		(gas or agent or chemical))	DERWENT	
-	96	((((diffus\$6 adj barrier) or prevent\$10)	USPAT;	2001/12/18 12:54
		adj (layer or film))) and (reduc\$4 adj	EPO; JPO;	
-		(gas or agent or chemical))) and (metal	DERWENT	
_	20851	<pre>adj (film or layer)) (((diffus\$6 adj barrier) or prevent\$10)</pre>	USPAT;	2001/12/18 14:02
-	20031	adj (layer or film))	EPO; JPO;	2001/12/10 14.02
		adj (lajol ol llim,,	DERWENT	
-	3447	(((diffus\$6 adj barrier) or (diffus\$6 adj	USPAT;	2001/12/18 14:04
		prevent\$10)) adj (layer or film))	EPO; JPO;	
		(((())))	DERWENT	0001/10/10 14 07
-	40	((((diffus\$6 adj barrier) or prevent\$10) adj (layer or film))) and (first adj	USPAT; EPO; JPO;	2001/12/18 14:07
1		anneal\$5)	DERWENT	
_	0		USPAT;	2001/12/18 14:08
		adj (layer or film))) and (first adj	EPO; JPO;	
		anneal\$5)) and (second adj aneal\$5)	DERWENT	
-	45418	barrier adj (layer or film)	USPAT;	2003/03/07 13:53
			EPO; JPO; DERWENT	
_	147	(barrier adj (layer or film)) and (first	USPAT;	2001/12/18 14:08
1		adj anneal\$5)	EPO; JPO;	
			DERWENT	
-	0	' '	USPAT;	2001/12/18 14:21
		adj anneal\$5)) and (second adj aneal\$5)	EPO; JPO; DERWENT	
	483098	plug or interconnection	USPAT;	2001/12/18 14:23
	403030	plug of interconnection	EPO; JPO;	2001/12/10 14.25
			DERWENT	
-	108014	metal adj (layer or film)	USPAT;	2001/12/18 14:24
			EPO; JPO;	
	18975	(metal adj (layer or film)) and (plug or	DERWENT USPAT;	2001/12/18 14:25
-	109/3	interconnect\$5)	EPO; JPO;	2001/12/10 14.25
			DERWENT	
-	3544	((metal adj (layer or film)) and (plug or	USPAT;	2001/12/18 14:25
:		interconnect\$5)) and anneal\$5	EPO; JPO;	
_	56	(((metal adj (layer or film)) and (plug or	DERWENT USPAT;	2001/12/18 14:30
	30	interconnect\$5)) and anneal\$5) and	EPO; JPO;	2001/12/16 14:30
		(reduc\$3 adj atmosphere)	DERWENT	
-	6	((barrier adj (layer or film)) and (first	USPAT;	2001/12/18 14:31
]		adj anneal\$5)) and (reduc\$3 adj	EPO; JPO;	
_	40	atmosphere) ((((metal adj (layer or film)) and (plug	DERWENT	2001/12/18 14:37
-	40	or interconnect\$5)) and anneal\$5) and	USPAT; EPO; JPO;	2001/12/18 14:3/
		(reduc\$3 adj atmosphere)) and	DERWENT	
		semiconductor		
-	6	, , , ,	USPAT;	2001/12/18 14:36
		(first adj anneal\$5)) and (reduc\$3 adj	EPO; JPO;	
_	5	atmosphere)) and semiconductor (("5116463") or ("6207222") or ("6197688")	DERWENT USPAT	2004/03/02 12:52
		or ("6191031") or ("6143646")).PN.	JULMI	2004/03/02 12:32
-	562	438/687	USPAT;	2004/02/20 13:52
			EPO; JPO;	
	55300	hamilan add (1ac 613)	DERWENT	0000/00/10 55 55
-	55733	barrier adj (layer or film)	USPAT;	2003/03/10 07:56
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	489	(barrier adj (layer or film)) and (reduc\$3	USPAT;	2003/03/07 14:01
		adj (gas or ambient))	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
·				i

-	160	(reduc\$3 adj (gas or ambient))) and (metal	USPAT; US-PGPUB;	2003/03/07 14:03
		adj (layer or film))	EPO; JPO; DERWENT; IBM TDB	
-	3	(reduc\$3 adj (gas or ambient))) and (metal	USPĀT; US-PGPUB;	2003/03/07 14:08
		<pre>adj (layer or film))) and (second adj (gas or ambient))</pre>	EPO; JPO; DERWENT; IBM TDB	
_	222	(barrier adj (layer or film)) and (reduc\$3 adj (gas or ambient)) and plasma	USPĀT; US-PGPUB; EPO; JPO;	2003/03/07 14:05
			DERWENT; IBM_TDB	
-	3	(((((barrier adj (layer or film)) and (reduc\$3 adj (gas or ambient))) and (metal adj (layer or film))) and (second adj (gas	USPAT; US-PGPUB; EPO; JPO;	2003/03/07 13:59
	112	or ambient))) and plasma	DERWENT; IBM_TDB USPAT;	2003/03/07 14:06
_	113	(((barrier adj (layer or film)) and (reduc\$3 adj (gas or ambient))) and (metal adj (layer or film))) and plasma	US-PGPUB; EPO; JPO; DERWENT;	2003/03/07 14:06
_	28226	(barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or	IBM_TDB USPAT; US-PGPUB;	2003/03/07 14:03
		ambient))	EPO; JPO; DERWENT;	
-	6490	((barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2")) adj	IBM_TDB USPAT; US-PGPUB;	2003/03/07 14:05
		(gas or ambient))) and (metal adj (layer or film))	EPO; JPO; DERWENT; IBM TDB	
-	222	((barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient))) and (reduc\$3 adj (gas	USPAT; US-PGPUB; EPO; JPO;	2003/03/07 14:07
		or ambient)) and plasma	DERWENT; IBM_TDB	
-	8105	((barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient))) and plasma	USPĀT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/07 14:07
_	3403	(((barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient))) and (metal adj (layer	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/03/07 14:07
	99	or film))) and plasma	DERWENT; IBM_TDB USPAT;	2003/03/07 14:07
	39	(reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient))) and (metal adj (layer	US-PGPUB; EPO; JPO;	2003/03/07 14:07
_	99	or film))) and (second adj (gas or ambient)) ((((barrier adj (layer or film)) and	DERWENT; IBM_TDB USPAT;	2003/03/07 14:10
		<pre>(reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient))) and (metal adj (layer or film))) and (second adj (gas or ambient))) and (second adj (gas or</pre>	US-PGPUB; EPO; JPO; DERWENT; IBM TDB	
_	92	<pre>ambient)) (((((barrier adj (layer or film)) and</pre>	USPAT;	2003/03/07 14:10
		<pre>(reduc\$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient))) and (metal adj (layer or film))) and (second adj (gas or</pre>	US-PGPUB; EPO; JPO; DERWENT;	
_	25099	<pre>ambient))) and (second adj (gas or ambient))) and semiconductor barrier adj (layer or film)</pre>	IBM_TDB USPAT	2003/03/10 07:56
_	7320	(barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj	USPAT	2003/03/10 07:36
		gases) or (hydrogen or ("H.sub.2"))))		

-	3856		USPAT	2003/03/10 08:02
		((expos\$3 or anneal\$5) and ((reduc\$3 adj		
		gases) or (hydrogen or ("H.sub.2"))))) and		
	1.004	semiconductor	USPAT	2003/03/10 08:03
_	1694	(((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj	USPAI	2003/03/10 08:03
		gases) or (hydrogen or ("H.sub.2"))))) and		
		semiconductor) and (metal adj (layer or		
		film))		
l -	303	1 ' '	USPAT	2003/03/10 08:04
		((expos\$3 or anneal\$5) and ((reduc\$3 adj		
		gases) or (hydrogen or ("H.sub.2"))))) and		
		semiconductor) and ((metal adj (layer or		
		film)) same (chemical adj vapor adj		
		deposition))		0000 /00 /10 00 05
-	60		USPAT	2003/03/10 08:05
		((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and		
		semiconductor) and (metal adj (layer or		
	i	film))) and (second adj gas)		
_	9		USPAT	2004/02/20 13:52
		((expos\$3 or anneal\$5) and ((reduc\$3 adj		
		gases) or (hydrogen or ("H.sub.2"))))) and		
]	semiconductor) and ((metal adj (layer or		
		film)) same (chemical adj vapor adj		
	_	deposition))) and (second adj gas)		0004/00/00 00 50
_	2		USPAT	2004/02/23 09:53
-	1	("6475902").PN.	USPAT	2003/11/17 07:10
-	1 3	("20020009872").PN. (("20020022354") or ("6248633") or	US-PGPUB USPAT;	2003/11/14 16:12 2003/11/17 06:46
-	3	((20020022334) 61 (6246633) 61 (6303959")).PN.	US-PGPUB	2003/11/17 00.40
_	10		USPAT	2004/02/20 13:53
	10	((expos\$3 or anneal\$5) and ((reduc\$3 adj	001111	2001, 02, 20 20100
		gases) or (hydrogen or ("H.sub.2"))))) and	Ì	
		semiconductor) and ((metal adj (layer or		
		film)) same (chemical adj vapor adj		
		deposition))) and (second adj gas)		
-	1661	438/687	USPAT;	2004/02/20 13:52
	İ		US-PGPUB; EPO; JPO;	
			DERWENT;	
		•	IBM TDB	
_	1884	438/618	USPAT;	2004/02/20 13:52
		100,000	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		,	IBM_TDB	0004400455 55 55
-	1281	438/633	USPAT;	2004/02/20 13:52
			US-PGPUB;	
			EPO; JPO; DERWENT;	
-			IBM TDB	
-	1407	438/627	USPAT;	2004/02/20 13:53
	1.07		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1772	438/643	USPAT;	2004/02/20 13:53
-			US-PGPUB;	
			EPO; JPO;	
1			DERWENT; IBM TDB	
_	1661	438/687	USPAT;	2004/02/20 13:53
	1001	1.00,00	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

	y			1000 400 400 00
-	2	438/687,618,633,627,643,687.CCLS. and	USPAT;	2004/03/02 13:03
		((((barrier adj (layer or film)) and	US-PGPUB;	
		((expos\$3 or anneal\$5) and ((reduc\$3 adj	EPO; JPO;	
	İ	gases) or (hydrogen or ("H.sub.2"))))) and	DERWENT;	
		semiconductor) and ((metal adj (layer or	IBM_TDB	
		film)) same (chemical adj vapor adj		
		deposition))) and (second adj gas) and @ad<=20010417		
_	8	438/\$.CCLS. and ((((barrier adj (layer or	USPAT;	2004/02/20 13:58
i ⁻		film)) and ((expos\$3 or anneal\$5) and	US-PGPUB;	2004/02/20 13:30
		((reduc\$3 adj gases) or (hydrogen or	EPO; JPO;	
		("H.sub.2"))))) and semiconductor) and	DERWENT;	
		((metal adj (layer or film)) same	IBM TDB	
		(chemical adj vapor adj deposition))) and	_	
1		(second adj gas) and @ad<=20010417		
_	8	257/\$.CCLS. and ((((barrier adj (layer or	USPAT;	2004/02/20 13:59
		film)) and ((expos\$3 or anneal\$5) and	US-PGPUB;	
		((reduc\$3 adj gases) or (hydrogen or	EPO; JPO;	
		("H.sub.2"))))) and semiconductor) and	DERWENT;	
		((metal adj (layer or film)) same	IBM_TDB	
		(chemical adj vapor adj deposition))) and		
]		(second adj gas) and @ad<=20010417	HODE	2004/02/20 12 52
_	11	((((barrier adj (layer or film)) and	USPAT;	2004/02/20 13:59
		((expos\$3 or anneal\$5) and ((reduc\$3 adj	US-PGPUB;	
		gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or	EPO; JPO; DERWENT;	
		semiconductor) and ((metal ad) (layer or film)) same (chemical adj vapor adj	IBM TDB	
		deposition))) and (second adj gas) and	I IBM_IBB	
		@ad<=20010417		
_	5	("5139825" "5178911" "5856236"	USPAT	2004/02/23 08:02
		"5900498" "5908947").PN.	,	
_	2508	(barrier adj (layer or film)) and	USPAT;	2004/03/02 09:01
		(reduc\$4) and (metal adj (layer or film))	EPO; JPO;	
		and (treat\$6 or ((post adj treat\$6) or	DERWENT	
		(post-treat\$6) or (posttreat\$6)))		
-	2198	(barrier adj (layer or film)) and	USPAT;	2004/03/02 09:02
		(reduc\$4) and (metal adj (layer or film))	EPO; JPO;	
		and (treat\$6 or ((post adj treat\$6) or	DERWENT	<u> </u>
		(post-treat\$6) or (posttreat\$6))) and		
	1.610	@ad<=20010417	HCDAM.	2004/03/02 09:12
_	1612	semiconductor and (barrier adj (layer or	USPAT; EPO; JPO;	2004/03/02 09:12
		film)) and (reduc\$4) and (metal adj (layer or film)) and (treat\$6 or ((post adj	DERWENT	
		treat\$6) or (post-treat\$6) or	DEKWENT	
		(posttreat\$6))) and @ad<=20010417		
_	1416	(semiconductor and (barrier adj (layer or	USPAT;	2004/03/02 09:13
		film)) and (reduc\$4) and (metal adj (layer	EPO; JPO;	
		or film)) and (treat\$6 or ((post adj	DERWENT	
		treat\$6) or (post-treat\$6) or	1	
		(posttreat\$6))) and @ad<=20010417) and		
		expos\$6		
-	1416		USPAT;	2004/03/02 09:15
1		film)) and (reduc\$4) and (metal adj (layer	EPO; JPO;	
	1	or film)) and (treat\$6 or ((post adj	DERWENT	
1		treat\$6) or (post-treat\$6) or		
		(posttreat\$6))) and @ad<=20010417) and		
		expos\$6) and reduc\$6	HCDATT	2004/02/02 12:52
1 _			USPAT	2004/03/02 12:53
1 -	1 2	("5,665,659").PN. 438/687,618,633,627,643,687.CCLS. and	USPAT;	2004/03/02 12:53
	2	((((barrier adj (layer or film)) and	US-PGPUB;	2004/03/00 00.00
		((expos\$3 or anneal\$5) and ((reduc\$3 adj	EPO; JPO;	
		gases) or (hydrogen or ("H.sub.2")))) and	DERWENT;	
		semiconductor) and ((metal adj (layer or	IBM TDB	
		film)) same (chemical adj vapor adj	_	
		deposition))) and (second adj gas) and		
		@ad<=20010417		